Method for Forming a Metal Oxide Semiconductor Type Field Effect Transistor

ABSTRACT OF THE INVENTION

This invention relates to a method for forming a metal oxide semiconductor type field effect transistor (MOSFET), more particularly, to the method for forming the MOSFET by forming a gate and a spacer in a trench. The present invention is used to form the gate and the spacer of the MOSFET in the trench which is preformed in the substrate to reduce the junction depth of the source/drain region. The present invention also can reduce the defects in the drain induced barrier lowering and the punch-through leakage to avoid the spiking leakage defects in the back-end process.